

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Low Frequency Noise: A Show Stopper for State-of-the-art and Future Si, Ge-based and III-V Technologies. , 2021, , .		0
2	Improved physics-based analysis to discriminate the flicker noise origin at very low temperature and drain voltage polarization. Solid-State Electronics, 2020, 171, 107771.	1.4	2
3	Electrical Activity of Extended Defects in Relaxed In _x Ga _{1-x} As Hetero-Epitaxial Layers. ECS Journal of Solid State Science and Technology, 2020, 9, 033001.	1.8	2
4	Are Extended Defects a Show Stopper for Future III-V CMOS Technologies. Journal of Physics: Conference Series, 2019, 1190, 012001.	0.4	1
5	Comparison between proton irradiated triple gate SOI TFETs and finfets from a TID point of view. Semiconductor Science and Technology, 2019, 34, 065003.	2.0	2
6	Low-Frequency Noise Assessment of Work Function Engineering Cap Layers in High-k Gate Stacks. ECS Journal of Solid State Science and Technology, 2019, 8, N25-N31.	1.8	12
7	Advanced CMOS Integration Technologies for Future Mobile Applications. , 2019, , .		1
8	Can we optimize the gate oxide quality of DRAM input/output pMOSFETs by a post-deposition treatment?. Semiconductor Science and Technology, 2019, 34, 015017.	2.0	0
9	Low Frequency Noise Analysis of Impact of Metal Gate Processing on the Gate Oxide Stack Quality. ECS Journal of Solid State Science and Technology, 2018, 7, Q26-Q32.	1.8	8
10	Ground Plane Impact on the Threshold Voltage of Relaxed Ge pFinFETs. , 2018, , .		0
11	Performance of differential pair circuits designed with line tunnel FET devices at different temperatures. Semiconductor Science and Technology, 2018, 33, 075012.	2.0	5
12	Random telegraph signal noise in advanced high performance and memory devices. , 2016, , .		4
13	Split CV mobility at low temperature operation of Ge pFinFETs fabricated with STI first and last processes. Semiconductor Science and Technology, 2016, 31, 114002.	2.0	2
14	Low frequency noise and fin width study of silicon passivated germanium pFinFETs. , 2016, , .		1
15	Effective hole mobility and low-frequency noise characterization of Ge pFinFETs. , 2016, , .		4
16	Analog parameters of solid source Zn diffusion In _x Ga _{1-x} As nTFETs down to 10 K. Semiconductor Science and Technology, 2016, 31, 124001.	2.0	5
17	Low Temperature Effect on Strained and Relaxed Ge pFinFETs STI Last Processes. ECS Transactions, 2016, 75, 213-218.	0.5	3
18	Low-Frequency Noise Assessment of the Oxide Trap Density in Thick-Oxide Input-Output Transistors for DRAM Applications. ECS Journal of Solid State Science and Technology, 2016, 5, N27-N31.	1.8	11

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19	Understanding and optimizing the floating body retention in FDSOI UTBOX. Solid-State Electronics, 2016, 117, 123-129.	1.4	4
20	Random telegraph noise: The key to single defect studies in nano-devices. Thin Solid Films, 2016, 613, 2-5.	1.8	8
21	Reviewâ€”Device Assessment of Electrically Active Defects in High-Mobility Materials. ECS Journal of Solid State Science and Technology, 2016, 5, P3149-P3165.	1.8	18
22	Performance of TFET and FinFET devices applied to current mirrors for different dimensions and temperatures. Semiconductor Science and Technology, 2016, 31, 055001.	2.0	10
23	Enhanced dynamic threshold voltage UTBB SOI nMOSFETs. Solid-State Electronics, 2015, 112, 19-23.	1.4	10
24	High temperature influence on analog parameters of Bulk and SOI nFinFETs. , 2015, , .		1
25	(Invited) Advanced Semiconductor Devices for Future CMOS Technologies. ECS Transactions, 2015, 66, 49-60.	0.5	3
26	Proton Radiation Effects on the Analog Performance of Bulk n- and p-FinFETs. ECS Transactions, 2015, 66, 295-301.	0.5	3
27	Comparison of Current Mirrors Designed with TFET or FinFET Devices for Different Dimensions and Temperatures. ECS Transactions, 2015, 66, 303-308.	0.5	2
28	Low frequency noise spectroscopy in rotated UTBOX nMOSFETs. , 2015, , .		8
29	Low-frequency noise study of Ge p-MOSFETs with $\text{HfO}_2/\text{Al}_2\text{O}_3/\text{GeO}_x$ gate stack. , 2015, , .		1
30	Detailed analysis of transport properties of FinFETs through Y-Function method: Effects of substrate orientation and strain. , 2015, , .		1
31	Impact of processing and back-gate biasing conditions on the low-frequency noise of ultra-thin buried oxide silicon-on-insulator nMOSFETs. Solid-State Electronics, 2015, 105, 37-44.	1.4	4
32	DC and noise characteristics of underlap Ultra-Thin BOX SOI nMOSFETs. , 2015, , .		0
33	Identification of Si film traps in p-channel SOI FinFETs using low temperature noise spectroscopy. Solid-State Electronics, 2015, 112, 1-6.	1.4	10
34	Static and low frequency noise characterization in standard and rotated UTBOX nMOSFETs. , 2015, , .		3
35	Effect of extension architecture on the LF noise of UTBOX SOI MOSFETs. , 2015, , .		0
36	The smaller the noisier? Low frequency noise diagnostics of advanced semiconductor devices. , 2015, , .		2

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37	Different stress techniques and their efficiency on triple-gate SOI n-MOSFETs. Solid-State Electronics, 2015, 103, 209-215.	1.4	3
38	Impact of Pre- and Post-Growth Treatment on the Low-Frequency Noise of InGaAs nMOSFETs. ECS Transactions, 2014, 60, 115-120.	0.5	2
39	Ground plane influence on enhanced dynamic threshold UTBB SOI nMOSFETs. , 2014, , .		6
40	Low frequency noise characterization of advanced and end of the roadmap devices. , 2014, , .		2
41	Geometry Dependence of Total-Dose Effects in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2951-2958.	2.0	54
42	Analog performance of standard and uniaxial strained triple-gate SOI FinFETs under x-ray radiation. Semiconductor Science and Technology, 2014, 29, 125015.	2.0	2
43	Study of Random Telegraph Noise in UTBOX Silicon-on-Insulator nMOSFETs. ECS Transactions, 2014, 60, 109-114.	0.5	3
44	Low-Frequency-Noise-Based Oxide Trap Profiling in Replacement High- κ /Metal-Gate pMOSFETs. ECS Journal of Solid State Science and Technology, 2014, 3, Q127-Q131.	1.8	11
45	Performances under saturation operation of p-channel FinFETs on SOI substrates at cryogenic temperature. , 2014, , .		2
46	In depth static and low-frequency noise characterization of n-channel FinFETs on SOI substrates at cryogenic temperature. Solid-State Electronics, 2014, 98, 12-19.	1.4	12
47	Defect assessment and leakage control in Ge junctions. Microelectronic Engineering, 2014, 125, 33-37.	2.4	18
48	Low-frequency noise assessment in advanced UTBOX SOI nMOSFETs with different gate dielectrics. Solid-State Electronics, 2014, 97, 14-22.	1.4	28
49	Improved retention times in UTBOX nMOSFETs for 1T-DRAM applications. Solid-State Electronics, 2014, 97, 30-37.	1.4	8
50	Impact of oxide trap passivation by fluorine on the low-frequency noise behavior of gate-last pMOSFETs. , 2013, , .		4
51	Low frequency noise characterization in n-channel UTBOX devices with 6 nm Si film. , 2013, , .		6
52	Detailed characterisation of SOI n-FinFETs at very low temperature. , 2013, , .		2
53	Analysis of border traps in high- κ gate dielectrics on high-mobility channels. , 2013, , .		0
54	Potential and limitations of UTBB SOI for advanced CMOS technologies. , 2013, , .		5

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55	Study of the impact of doping concentration and Schottky barrier height on ohmic contacts to n-type germanium. Microelectronic Engineering, 2013, 106, 129-131.	2.4	8
56	Drain currents and their excess noise in triple gate bulk p-channel FinFETs of different geometry. Microelectronics Reliability, 2013, 53, 394-399.	1.7	0
57	NW-TFET analog performance for different Ge source compositions. , 2013, , .		11
58	Comparative Experimental Study between Tensile and Compressive Uniaxially Stressed nMuGFETs under X-ray Radiation Focusing on Analog Behavior. ECS Transactions, 2013, 53, 177-185.	0.5	0
59	Semiconductor Film Bandgap Influence on Retention Time of UTBOX SOI 1T-FBRAM. ECS Transactions, 2013, 53, 139-146.	0.5	2
60	Low-Frequency Noise in High-K and SiO ₂ UTBOX SOI nMOSFETs. ECS Transactions, 2013, 52, 87-92.	0.5	1
61	The Generation Rate Analysis of Different S/D Junction Engineering in Scaled UTBOX 1T-DRAM. ECS Transactions, 2013, 53, 195-201.	0.5	2
62	(Invited) Status and Trends in Ge CMOS Technology. ECS Transactions, 2013, 54, 25-37.	0.5	19
63	Lessons Learned from Low-Frequency Noise Studies on Fully Depleted UTBOX Silicon-On-Insulator nMOSFETs. ECS Transactions, 2013, 53, 49-61.	0.5	6
64	Low-Frequency-Noise-Based Oxide Trap Profiling in Replacement High-k/Metal-Gate pMOSFETs. ECS Transactions, 2013, 58, 281-292.	0.5	3
65	Low-Frequency Noise Studies on Fully Depleted UTBOX Silicon-on-Insulator nMOSFETs: Challenges and Opportunities. ECS Journal of Solid State Science and Technology, 2013, 2, Q205-Q210.	1.8	14
66	Influence of X-ray radiation on standard and uniaxial strained triple-gate SOI FinFETs. , 2013, , .		2
67	Impact of Disturb on Retention Time in Single FBRAM Cells. ECS Meeting Abstracts, 2013, , .	0.0	1
68	On the Variability of the Low-Frequency Noise in UTBOX SOI nMOSFETs. ECS Transactions, 2012, 49, 51-58.	0.5	3
69	Uniaxial and/or Biaxial Strain Influence on MuGFET Devices. Journal of the Electrochemical Society, 2012, 159, H570-H574.	2.9	0
70	Spacer Length and Tilt Implantation Influence on Scaled UTBOX FD MOSFETs. ECS Transactions, 2012, 49, 483-489.	0.5	1
71	Biaxial + uniaxial stress effectiveness in tri-gate SOI nMOSFETs with variable fin dimensions. , 2012, , .		1
72	Origin of wide retention distribution in 1T Floating Body RAM. , 2012, , .		7

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73	Uniaxial mechanical stress influence on the low frequency noise in FD SOI nMOSFETs operating in saturation. , 2012, , .		0
74	Gate length impact on UTBOX FBRAM devices. , 2012, , .		2
75	Challenges and opportunities in advanced Ge pMOSFETs. Materials Science in Semiconductor Processing, 2012, 15, 588-600.	4.0	72
76	Low-Frequency Noise Assessment of the Oxide Quality of Gate-Last High- k pMOSFETs. IEEE Electron Device Letters, 2012, 33, 1366-1368.	3.9	8
77	High-energy neutrons effect on strained and non-strained SOI MuGFETs and planar MOSFETs. Microelectronics Reliability, 2012, 52, 118-123.	1.7	2
78	Low frequency noise characterization in n-channel FinFETs. Solid-State Electronics, 2012, 70, 20-26.	1.4	27
79	GIDL behavior of p- and n-MuGFET devices with different TiN metal gate thickness and high-k gate dielectrics. Solid-State Electronics, 2012, 70, 44-49.	1.4	6
80	Radiation damage of Si $_{1-x}$ Ge $_x$ S/D p-type metal oxide semiconductor field effect transistor with different Ge concentrations. Thin Solid Films, 2012, 520, 3337-3340.	1.8	9
81	Laser- and Heavy Ion-Induced Charge Collection in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2011, 58, 2563-2569.	2.0	58
82	Ge content and recess depth dependence of the band-to-band tunneling current in Si $_{1-x}$ Ge $_x$ /Ge $_x$ /Si hetero-junctions. , 2011, , .		0
83	Assessment of temperature dependence of the low frequency noise in unstrained and strained FinFETs. , 2011, , .		3
84	Low-frequency noise in triple-gate n-channel bulk FinFETs. , 2011, , .		7
85	Impact of proton irradiation on strained triple gate SOI p- and n-MOSFETs. , 2011, , .		3
86	Study of ohmic contacts to n-type Ge: Snowplow and laser activation. Applied Physics Letters, 2011, 99, .	3.3	32
87	Investigation of Tri-Gate FinFETs by Noise Methods. Engineering Materials, 2011, , 287-306.	0.6	1
88	Defect-Related Excess Low-Frequency Noise in Ge-on-Si pMOSFETs. IEEE Electron Device Letters, 2011, 32, 87-89.	3.9	10
89	Pulsed laser-induced transient currents in bulk and silicon-on-insulator FinFETs. , 2011, , .		12
90	Low-Frequency Noise Characterization of Strained Germanium pMOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 3132-3139.	3.0	19

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91	Influence of the sidewall crystal orientation, HfSiO nitridation and TiN metal gate thickness on n-MuGFETs under analog operation. Solid-State Electronics, 2011, 62, 146-151.	1.4	4
92	Evaluation of electron irradiated embedded SiGe source/drain diodes by Raman spectroscopy. Microelectronic Engineering, 2011, 88, 484-487.	2.4	3
93	Gate-edge charges related effects and performance degradation in advanced multiple-gate MOSFETs. Solid-State Electronics, 2011, 59, 18-24.	1.4	11
94	LKE and BGI Lorentzian noise in strained and non-strained tri-gate SOI FinFETs with HfSiON/SiO ₂ gate dielectric. Solid-State Electronics, 2011, 63, 27-36.	1.4	0
95	Uniaxial stress efficiency for different fin dimensions of triple-gate SOI nMOSFETs. , 2011, , .		2
96	Analysis of the Temperature Dependence of Trap-Assisted Tunneling in Ge pFET Junctions. Journal of the Electrochemical Society, 2011, 158, H955.	2.9	17
97	High Doping Density/High Electric Field, Stress and Heterojunction Effects on the Characteristics of CMOS Compatible p-n Junctions. Journal of the Electrochemical Society, 2011, 158, R27.	2.9	21
98	SOI MOSFET Transconductance Behavior from Micro to Nano Era. Engineering Materials, 2011, , 267-286.	0.6	0
99	Degradation of GaN LEDs by electron irradiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 57-60.	3.5	15
100	Si versus Ge for future microelectronics. Thin Solid Films, 2010, 518, 2301-2306.	1.8	19
101	P+/n junction leakage in thin selectively grown Ge-in-STI substrates. Thin Solid Films, 2010, 518, 2489-2492.	1.8	11
102	Low-frequency noise assessment of the silicon passivation of Ge pMOSFETs. Thin Solid Films, 2010, 518, 2493-2496.	1.8	14
103	Short-channel epitaxial germanium pMOS transistors. Thin Solid Films, 2010, 518, S88-S91.	1.8	5
104	Effects of electron irradiation on SiGe devices. Thin Solid Films, 2010, 518, 2517-2520.	1.8	4
105	Device performance of p-Ge MOSFETs at liquid nitrogen temperature. Thin Solid Films, 2010, 518, 2513-2516.	1.8	0
106	Effect of rotation, gate-dielectric and SEG on the noise behavior of advanced SOI MuGFETs. Solid-State Electronics, 2010, 54, 178-184.	1.4	12
107	Low-frequency noise and static analysis of the impact of the TiN metal gate thicknesses on n- and p-channel MuGFETs. Solid-State Electronics, 2010, 54, 1592-1597.	1.4	10
108	Modeling impact of electric field and strain on the leakage of embedded SiGe source/drain junctions. , 2010, , .		1

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109	Zero-Temperature-Coefficient of planar and MuGFET SOI devices. , 2010, , .		7
110	Fin shape influence on the analog performance of standard and strained MuGFETs. , 2010, , .		8
111	Influence of Fin Width on the Total Dose Behavior of p-Channel Bulk MuGFETs. IEEE Electron Device Letters, 2010, 31, 243-245.	3.9	26
112	Extended-Defect Aspects of Ge-on-Si Materials and Devices. Journal of the Electrochemical Society, 2010, 157, R1.	2.9	12
113	Electrical-Based ESD Characterization of Ultrathin-Body SOI MOSFETs. IEEE Transactions on Device and Materials Reliability, 2010, 10, 130-141.	2.0	7
114	DIBL performance of 60 MeV proton-irradiated SOI MuGFETs. , 2010, , .		2
115	Analytical model for the $1/f$ noise in the tunneling current through metal-oxide-semiconductor structures. Journal of Applied Physics, 2009, 106, .	2.5	25
116	On the frequency dispersion of the capacitance-voltage behavior of epitaxial Ge on Si p+n junctions. Journal of Applied Physics, 2009, 106, 074511.	2.5	9
117	Electric field dependence of trap-assisted-tunneling current in strained SiGe source/drain junctions. Applied Physics Letters, 2009, 94, 233507.	3.3	7
118	Low-frequency Noise Analysis of the Impact of an LaO Cap Layer in HfSiON/Ta ₂ C Gate Stack nMOSFETs. ECS Transactions, 2009, 25, 237-245.	0.5	10
119	What Do We Know about Hydrogen-Induced Thermal Donors in Silicon?. Journal of the Electrochemical Society, 2009, 156, H434.	2.9	25
120	Low-Frequency Noise Behavior in P-channel SOI FinFETs Processed With Different Strain Techniques. , 2009, , .		3
121	On the $1/f$ noise of triple-gate field-effect transistors with high- k gate dielectric. Applied Physics Letters, 2009, 95, 032101.	3.3	16
122	Impact of the TiN Layer Thickness on the Low-Frequency Noise and Static Device Performance of n-Channel MuGFETs. , 2009, , .		0
123	Low-Frequency Noise of Strained and Non-Strained n-Channel Tri-Gate FinFETs With Different Gate Dielectrics. , 2009, , .		1
124	Linear kink effect Lorentzians in the noise spectra of n- and p-channel fin field-effect transistors processed in standard and strained silicon-on-insulator substrates. Solid-State Electronics, 2009, 53, 613-620.	1.4	2
125	Physics of fluctuation processes in downscaled silicon MOSFETs. Radiophysics and Quantum Electronics, 2009, 52, 655-670.	0.5	1
126	Strained Si/SiGe MOS technology: Improving gate dielectric integrity. Microelectronic Engineering, 2009, 86, 218-223.	2.4	24

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127	1/f noise study on strained Si _{0.8} Ge _{0.2} p-channel MOSFETs with high-k/poly Si gate stack. Solid-State Electronics, 2009, 53, 1177-1182.	1.4	0
128	Cryogenic operation of FinFETs aiming at analog applications. Cryogenics, 2009, 49, 590-594.	1.7	21
129	1/f Noise in Drain and Gate Current of MOSFETs With High-k Gate Stacks. IEEE Transactions on Device and Materials Reliability, 2009, 9, 180-189.	2.0	107
130	Reliability performance characterization of SOI FinFETs. , 2009, , .		1
131	Impact of TiN metal gate thickness and the HfSiO nitridation on MuGFETs electrical performance. , 2009, , .		0
132	On the Temperature and Field Dependence of Trap-Assisted Tunneling Current in Ge p^+n Junctions. IEEE Electron Device Letters, 2009, 30, 562-564.	3.9	49
133	High gate voltage drain current leveling off and its low-frequency noise in 65nm fully-depleted strained and non-strained SOI nMOSFETs. Solid-State Electronics, 2008, 52, 801-807.	1.4	6
134	Impact of strain and source/drain engineering on the low frequency noise behaviour in n-channel tri-gate FinFETs. Solid-State Electronics, 2008, 52, 1889-1894.	1.4	21
135	Carrier lifetime analysis in thin gate oxide FD-SOI n-MOSFETs by gate-induced drain current transients. Journal of Materials Science: Materials in Electronics, 2008, 19, 161-165.	2.2	0
136	Degradation of SiC-MESFETs by irradiation. Journal of Materials Science: Materials in Electronics, 2008, 19, 175-178.	2.2	0
137	Effects of electron and proton irradiation on embedded SiGe source/drain diodes. Materials Science in Semiconductor Processing, 2008, 11, 310-313.	4.0	4
138	Impact strain engineering on gate stack quality and reliability. Solid-State Electronics, 2008, 52, 1115-1126.	1.4	69
139	Defect engineering aspects of advanced Ge process modules. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 49-55.	3.5	14
140	Radiation damage in proton-irradiated strained Si n-MOSFETs. Materials Science in Semiconductor Processing, 2008, 11, 314-318.	4.0	4
141	Stress analysis of Si _{1-x} Ge _x embedded source/drain junctions. Materials Science in Semiconductor Processing, 2008, 11, 285-290.	4.0	7
142	Influence of the pre-treatment anneal on Co ²⁺ germanide Schottky contacts. Materials Science in Semiconductor Processing, 2008, 11, 300-304.	4.0	6
143	Impact of Donor Concentration, Electric Field, and Temperature Effects on the Leakage Current in Germanium p^+n Junctions. IEEE Transactions on Electron Devices, 2008, 55, 2287-2296.	3.0	69
144	Paramagnetic point defects at interfacial layers in biaxial tensile strained (100)Si/SiO ₂ . Journal of Applied Physics, 2008, 103, .	2.5	17

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145	Processing Factors Impacting the Leakage Current and Flicker Noise of Germanium p ⁺ -n Junctions on Silicon Substrates. Journal of the Electrochemical Society, 2008, 155, H145.	2.9	9
146	Improved generation lifetime model for the electrical characterization of single- and double-gate SOI nMOSFETs. Semiconductor Science and Technology, 2008, 23, 125011.	2.0	5
147	Study of metal-related deep-level defects in germanide Schottky barriers on n-type germanium. Journal of Applied Physics, 2008, 104, .	2.5	22
148	Low temperature noise spectroscopy of 0.1 μ m partially depleted silicon on insulator metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2007, 101, 104511.	2.5	45
149	Behavior of the 1/f noise and electron mobility in 65 nm FD SOI nMOSFETs employing different tensile-strain-inducing techniques. AIP Conference Proceedings, 2007, .	0.4	3
150	The Low-Frequency Noise Behavior of pMOSFETs with Embedded SiGe Source/Drain Regions. AIP Conference Proceedings, 2007, .	0.4	1
151	The Length-Dependence of the 1/f Noise of Graded-Channel SOI nMOSFETs. ECS Transactions, 2007, 9, 373-381.	0.5	1
152	On the Low-Frequency Noise of pMOSFETs With Embedded SiGe Source/Drain and Fully Silicided Metal Gate. IEEE Electron Device Letters, 2007, 28, 987-989.	3.9	19
153	On the origin of the 1/f noise in shallow germanium p+n junctions. Applied Physics Letters, 2007, 90, 043501.	3.3	6
154	Leakage Current Control in Recessed SiGe Source/Drain Junctions. Journal of the Electrochemical Society, 2007, 154, H814.	2.9	12
155	Low Temperature Operation of Undoped Body Triple-Gate FinFETs from an Analog Perspective. ECS Transactions, 2007, 9, 19-27.	0.5	1
156	Analysis of the Pre-epi Bake Conditions on the Defect Creation in Recessed SiGe S/D Junctions. ECS Transactions, 2007, 11, 47-53.	0.5	3
157	Low-Frequency Noise Assessment of Silicon Passivated Ge pMOSFETs With TiN/TaN/ HfO_2 Gate Stack. IEEE Electron Device Letters, 2007, 28, 288-291.	3.9	35
158	Analysis of junction leakage in advanced germanium P+/n junctions. , 2007, .		8
159	Geometry and Strain Dependence of the Proton Radiation Behavior of MuGFET Devices. IEEE Transactions on Nuclear Science, 2007, 54, 2227-2232.	2.0	29
160	On the Origin of the Excess Low-Frequency Noise in Graded-Channel Silicon-on-Insulator nMOSFETs. IEEE Electron Device Letters, 2007, 28, 919-921.	3.9	4
161	Low-frequency noise in silicon-on-insulator devices and technologies. Solid-State Electronics, 2007, 51, 16-37.	1.4	94
162	The low-frequency noise behaviour of graded-channel SOI nMOSFETs. Solid-State Electronics, 2007, 51, 260-267.	1.4	12

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163	Evaluation of triple-gate FinFETs with SiO ₂ /HfO ₂ /TiN gate stack under analog operation. Solid-State Electronics, 2007, 51, 285-291.	1.4	32
164	Impact of the gate-electrode/dielectric interface on the low-frequency noise of thin gate oxide n-channel metal-oxide-semiconductor field-effect transistors. Solid-State Electronics, 2007, 51, 627-632.	1.4	13
165	Gate induced floating body effects in TiN/SiON and TiN/HfO ₂ gate stack triple gate SOI nFinFETs. Solid-State Electronics, 2007, 51, 1201-1210.	1.4	5
166	Temperature impact on the Lorentzian noise induced by electron valence-band tunneling in partially depleted SOI p-MOSFETs. Solid-State Electronics, 2007, 51, 1180-1184.	1.4	2
167	Dose rate dependence of radiation-induced lattice defects and performance degradation in npn Si bipolar transistors by 2-MeV electron irradiation. Physica B: Condensed Matter, 2007, 401-402, 469-472.	2.7	4
168	Electrical stress on irradiated thin gate oxide partially depleted SOI nMOSFETs. Microelectronic Engineering, 2007, 84, 2081-2084.	2.4	8
169	Dose rate dependence of the back gate degradation in thin gate oxide PD-SOI MOSFETs by 2-MeV electron irradiation. Microelectronic Engineering, 2007, 84, 2125-2128.	2.4	5
170	Performance degradation mechanism of irradiated GaAlAs LED. Physica B: Condensed Matter, 2007, 401-402, 33-36.	2.7	0
171	Effect of gate interface on performance degradation of irradiated SiC-MESFET. Physica B: Condensed Matter, 2007, 401-402, 37-40.	2.7	2
172	A DLTS study on plasma-hydrogenated n-type high-resistivity magnetic Cz silicon. Journal of Materials Science: Materials in Electronics, 2007, 18, 705-710.	2.2	6
173	Lifetime and leakage current considerations in metal-doped germanium. Journal of Materials Science: Materials in Electronics, 2007, 18, 799-804.	2.2	16
174	Interfacial layer quality effects on low-frequency noise (1/f) in p-MOSFETs with advanced gate stacks. Microelectronics Reliability, 2007, 47, 501-504.	1.7	4
175	Low-frequency (1/f) noise behavior of locally stressed HfO ₂ /TiN gate-stack pMOSFETs. IEEE Electron Device Letters, 2006, 27, 508-510.	3.9	27
176	Impact of the interfacial layer on the low-frequency noise (1/f) behavior of MOSFETs with advanced gate stacks. IEEE Electron Device Letters, 2006, 27, 688-691.	3.9	54
177	Effect of Nitridation on Low-Frequency (1/f) Noise in n- and p-MOSFETs with HfO ₂ Gate Dielectrics. Journal of the Electrochemical Society, 2006, 153, C819.	2.9	12
178	Radiation-induced defects in SiC-MESFETs after 2-MeV electron irradiation. Physica B: Condensed Matter, 2006, 376-377, 382-384.	2.7	16
179	1/f noise performance of MOSFETs with HfO ₂ and metal gate on Ge-on-insulator substrates. Materials Science in Semiconductor Processing, 2006, 9, 721-726.	4.0	18
180	Radiation damage in electron-irradiated strained Si n-MOSFETs. Materials Science in Semiconductor Processing, 2006, 9, 732-736.	4.0	1

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181	A deep-level transient spectroscopy study of Co- and Ni-germanided n-type germanium. Materials Science in Semiconductor Processing, 2006, 9, 554-558.	4.0	12
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